L Number	Hits	Search Text	DB	Time stamp
1	159252	(USUI or HIDEKI or IGARASHI or	USPAT;	2004/07/02 13:43
		SAKAMOTO).in.	US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	215	((USUI or HIDEKI or IGARASHI or	USPAT;	2004/07/02 13:43
		SAKAMOTO).in.) and plasma same irradiat\$3	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	74	(((USUI or HIDEKI or IGARASHI or	USPAT;	2004/07/02 13:44
-		SAKAMOTO).in.) and plasma same irradiat\$3)	US-PGPUB;	
]		and (resin or polymer)	EPO; JPO;	
1			DERWENT;	
1	_		IBM_TDB	0004/07/00 13 45
4	5	((((USUI or HIDEKI or IGARASHI or	USPAT;	2004/07/02 13:45
		SAKAMOTO).in.) and plasma same irradiat\$3) and (resin or polymer)) and (resin or	US-PGPUB; EPO; JPO;	
		polymer) same (over or cover\$3) same (die	DERWENT;	
		or chip or IC or element or circuit)	IBM TDB	
5	11	438/106.ccls. and irradiat\$3 same plasma	USPAT;	2004/07/02 13:55
}		•	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
	500	400/507	IBM_TDB	2004/07/00 12:40
1-	522	438/597.ccls.	USPAT; US-PGPUB;	2004/07/02 13:42
			EPO; JPO;	
			DERWENT;	
	•		IBM TDB	
-	37	438/597.ccls. and resin and plasma	USPĀT;	2004/06/22 15:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	42	438/124.ccls. and plasma	IBM_TDB USPAT;	2004/06/22 15:16
-	42	436/124.CCIS. and plasma	US-PGPUB;	2004/00/22 13.10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(438/597.ccls. and resin and plasma) and	USPAT;	2004/06/22 15:17
		(438/124.ccls. and plasma) and	US-PGPUB;	
		((irradiating or plasma) same resin)	EPO; JPO;	
			DERWENT; IBM_TDB	
_	43	(438/597.ccls. and resin and plasma) or	USPĀT;	2004/06/22 15:17
		(438/124.ccls. and plasma) and	US-PGPUB;	
		((irradiating or plasma) same resin)	EPO; JPO;	
			DERWENT;	
	_	///20/507 0010 100 100 100 100 100 100 100 100	IBM_TDB	2004/06/22 15:20
-	6	((438/597.ccls. and resin and plasma) or (438/124.ccls. and plasma) and	USPAT; US-PGPUB;	2004/06/22 15:36
		((irradiating or plasma) same resin)) and	EPO; JPO;	
		rough\$5	DERWENT;	7
			IBM_TDB	1
-	4	6,596,559	USPAT;	2004/06/22 16:02
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2548	438/106.ccls.	<pre>IBM_TDB USPAT;</pre>	2004/06/22 16:05
	23,30	155,100.6615.	US-PGPUB;	
ľ		,	EPO; JPO;	
			DERWENT;	
	ĺ		IBM_TDB	000110=100
_	41	438/106.ccls. and rough\$6 and plasma	USPAT;	2004/07/02 13:55
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	<u> </u>	6713858.URPN.	USPAT	2004/06/22 17:21
L		1	,	

27	("3013926" "4211824" "4251409" "4388132" "4680228" "5002808" "5098618" "5104944" "5121190" "5147084" "5391650" "5583747" "5683757" "5745984" "5948484" "6074895" "6248614" "6259155" "6284050" "6288900" "6294741"	USPAT	2004/06/22 17:23
481	"6353420" "6512295" "6548909" "6596559" "6624507" "6642613").PN.	USPAT; US-PGPUB;	2004/06/23 10:26
407	(438/\$5.ccls. and resin and (openings same pads)) and (chip or die) and (top or over	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/23 10:26
104	or covering) ((438/\$5.ccls. and resin and (openings same pads)) and (chip or die) and (top or	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB:	2004/06/23 10:27
32	over or covering)) and exposing same pads (((438/\$5.ccls. and resin and (openings	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/23 10:27
3	over or covering)) and exposing same pads) and encapsulating ((((438/\$5.ccls. and resin and (openings	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/23 10:28
2	over or covering)) and exposing same pads) and encapsulating) and (O2 or oxygen) 6689641.pn.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/23 12:26
13	(US-6074895-\$ or US-5002808-\$ or	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/23 12:51
	US-6713858-\$ or US-6248655-\$ or US-6600224-\$ or US-6596559-\$ or US-6602803-\$ or US-5766979-\$ or US-6512295-\$ or US-4388132-\$ or US-6479409-\$ or US-6689641-\$).did. or	US-PGPUB	
1	(US-20020130397-\$).did. ((US-6074895-\$ or US-5002808-\$ or US-6713858-\$ or US-6248655-\$ or US-6600224-\$ or US-6596559-\$ or US-6602803-\$ or US-5766979-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 12:52
4	US-6512295-\$ or US-4388132-\$ or US-6479409-\$ or US-6689641-\$).did. or (US-20020130397-\$).did.) and (inert or helium or argon or neon).clm. ((US-6074895-\$ or US-5002808-\$ or	IBM_TDB USPAT;	2004/06/23 12:53
	US-6713858-\$ or US-6248655-\$ or US-6600224-\$ or US-6596559-\$ or US-6602803-\$ or US-5766979-\$ or US-6512295-\$ or US-4388132-\$ or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
0	(US-20020130397-\$).did.) and (inert or helium or argon or neon)	USPAT; US-PGPUB; EPO; JPO;	2004/06/23 16:40
7704	(438/15 or 438/106 or 438/118 or 438/108 or 438/121 or 438/778 or 438/780 or 438/790 or 438/780).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/02 11:52
	 407 104 32 3 2 13 4 0 	"5098618" "5104944" "5121190" "5147084" "5391650" "5583747" "5683757" "5745984" "5948484" "60074895" "6248614" "6259155" "6284050" "6288900" "6294741" "6353420" "6512295" "6542803" "6596559" "66224507" "6542613").PN. 438/\$5.ccls. and resin and (openings same pads) and (chip or die) and (top or over or covering) 104 ((438/\$5.ccls. and resin and (openings same pads)) and (chip or die) and (top or over or covering) and exposing same pads) and (chip or die) and (top or over or covering)) and exposing same pads) and encapsulating 3 ((((438/\$5.ccls. and resin and (openings same pads)) and (chip or die) and (top or over or covering)) and exposing same pads) and encapsulating 3 ((((438/\$5.ccls. and resin and (openings same pads)) and (chip or die) and (top or over or covering)) and exposing same pads) and encapsulating) and (O2 or oxygen) 2 6689641.pn. 13 (US-6074895-\$ or US-5002808-\$ or US-6600224-\$ or US-6596559-\$ or US-6600224-\$ or US-6596599-\$ or US-660203-\$ or US-6602080-\$ or US-66	"5098618" i "5104944" "5121190" "5147084" "5391650" "5583747" "5683757" "57455984" "5948484" "6074895" "624801" "6249741" "6353420" "6288900" "6249741" "63596559" "6628900" "6249741" "63596559" "6624507" "6648039" "6396559" "6624507" "6648039" "63965959" "6624507" "6489309" "63965959" "6624507" "6642613").PN. 407 (438/\$5.ccls. and resin and (openings same pads) and (chip or die) and (top or over or covering) 104 (438/\$5.ccls. and resin and (openings same pads) and (chip or die) and (top or over or covering) and exposing same pads) and (chip or die) and (top or over or covering) and exposing same pads) and (chip or die) and (top or over or covering) and exposing same pads) and encapsulating and encapsulating and encapsulating and (openings same pads) and (chip or die) and (top or over or covering)) and exposing same pads) and encapsulating

-	5	((438/15 or 438/106 or 438/118 or 438/108 or 438/121 or 438/778 or 438/780 or	USPAT; US-PGPUB;	2004/07/02 11:59
		438/790 or 438/780).ccls.	EPO; JPO;	
			DERWENT;	
_	1210) and (plasma adj irradiating) ((438/15 or 438/106 or 438/118 or 438/108	IBM_TDB USPAT;	2004/07/02 12:00
	1210	or 438/121 or 438/778 or 438/780 or	US-PGPUB;	2004/07/02 12:00
		438/790 or 438/780).ccls.	EPO; JPO;	
) and waltage	DERWENT; IBM TDB	
_	61) and voltage (((438/15 or 438/106 or 438/118 or	USPAT;	2004/07/02 12:00
		438/108 or 438/121 or 438/778 or 438/780	US-PGPUB;	
		or 438/790 or 438/780).ccls.	EPO; JPO; DERWENT;	
) and voltage) and (voltage same rf same	IBM_TDB	
		plasma)		0004/07/00 10 01
_	30	((((438/15 or 438/106 or 438/118 or 438/108 or 438/121 or 438/778 or 438/780	USPAT; US-PGPUB;	2004/07/02 12:01
		or 438/790 or 438/780).ccls.	EPO; JPO;	
		\	DERWENT;	
) and voltage) and (voltage same rf same plasma)) and (resin or polymer)	IBM_TDB	
-	28	(((((438/15 or 438/106 or 438/118 or	USPAT;	2004/07/02 12:11
	1	438/108 or 438/121 or 438/778 or 438/780 or 438/790 or 438/780).ccls.	US-PGPUB; EPO; JPO;	
		01 438/790 01 438/700).ccis.	DERWENT;	
) and voltage) and (voltage same rf same	IBM_TDB	
		plasma)) and (resin or polymer)) and conductive		
_	0	((438/15 or 438/106 or 438/118 or 438/108	USPAT;	2004/07/02 12:11
		or 438/121 or 438/778 or 438/780 or	US-PGPUB;	
		438/790 or 438/780).ccls.	EPO; JPO; DERWENT;	
) and (backside adj conductive adj layer)	IBM_TDB	
-	1	(((438/15 or 438/106 or 438/118 or 438/108 or 438/121 or 438/778 or 438/780	USPAT; US-PGPUB;	2004/07/02 12:14
		or 438/790 or 438/780).ccls.	EPO; JPO;	
			DERWENT;	
) or 438/597) and (backside adj conductive adj layer)	IBM_TDB	
-	. 11		USPAT;	2004/07/02 12:24
		layer)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	0004/07/00 50 55
_	80	conductive same polymer same substrate same bias	USPĀT; US-PGPUB;	2004/07/02 12:25
			EPO; JPO;	
			DERWENT; IBM TDB	
_	23	(conductive same polymer same substrate	USPAT;	2004/07/02 12:37
		same bias) and conductive and plasma	US-PGPUB;	
	-		EPO; JPO; DERWENT;	
			IBM_TDB	
-	15	1 '	USPĀT	2004/07/02 12:34
1		"5362358" "5368685" "5439849" "5441595" "5468341" "5614060"		
		"5683517" "5683538" "5877032"		
_	0	"5895740" "5942446" "6251791").PN. (irradiat\$3 adj plasma) same (voltage same	USPAT;	2004/07/02 12:38
		conductive same backside)	US-PGPUB;	2004,07,02 12.30
			EPO; JPO;	
			DERWENT; IBM TDB	
-	0	(irradiat\$3 adj plasma) and (voltage same	USPAT;	2004/07/02 12:39
		conductive same backside)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	

	0	// / / / / /	USPAT:	2004/07/02 12:39
=	0	(irradiat\$3 same plasma) and (voltage same	US-PGPUB;	2004/07/02 12:39
		conductive same backside)	1	
			EPO; JPO;	
			DERWENT;	
li .		//	IBM_TDB	2004/07/02 12:39
-	0	(taracarat o bamo pratima, and taracara	USPAT;	2004/07/02 12:39
		conductive same backside)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	8	I (manufacture, or training production)	USPAT;	2004/07/02 13:02
		(conductive same backside)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7	((table and) o table Familiary table table table	USPAT;	2004/07/02 12:39
		(conductive same backside)) and voltage	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	(irradiat\$3 same plasma) and ((metal or	USPAT;	2004/07/02 12:49
		conductive) same backside) and (resin or	US-PGPUB;	
		polymer)	EPO; JPO;	
		·	DERWENT;	1
			IBM_TDB	
-	53	(expos\$3 same plasma same (polymer or	USPAT;	2004/07/02 12:49
		resin)) and ((metal or conductive) same	US-PGPUB;	
1	1	backside)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4	((irradiat\$3 or expos\$3) same plasma) and	USPAT;	2004/07/02 13:03
		((connection same backside) same (cathode	US-PGPUB;	
		or anode))	EPO; JPO;	
			DERWENT;	
			IBM TDB	1